



US007288822B1

(12) **United States Patent**
Ting et al.

(10) **Patent No.:** **US 7,288,822 B1**
(45) **Date of Patent:** **Oct. 30, 2007**

(54) **SEMICONDUCTOR STRUCTURE AND
FABRICATING METHOD THEREOF**

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(*) Notice: Subject to any disclaimer, the term of this
patent is extended or adjusted under 35
U.S.C. 154(b) by 0 days.

(21) Appl. No.: **11/399,827**

(22) Filed: **Apr. 7, 2006**

(51) **Int. Cl.**
H01L 29/76 (2006.01)
H01L 29/94 (2006.01)
H01L 31/062 (2006.01)
H01L 31/113 (2006.01)
H01L 31/119 (2006.01)

(52) **U.S. Cl.** **257/371; 257/335; 257/338;**
257/341; 257/350; 257/351; 257/357; 257/369;
257/401

(58) **Field of Classification Search** **257/335,**
257/338, 341, 350-351, 357, 369, 371, 401
See application file for complete search history.

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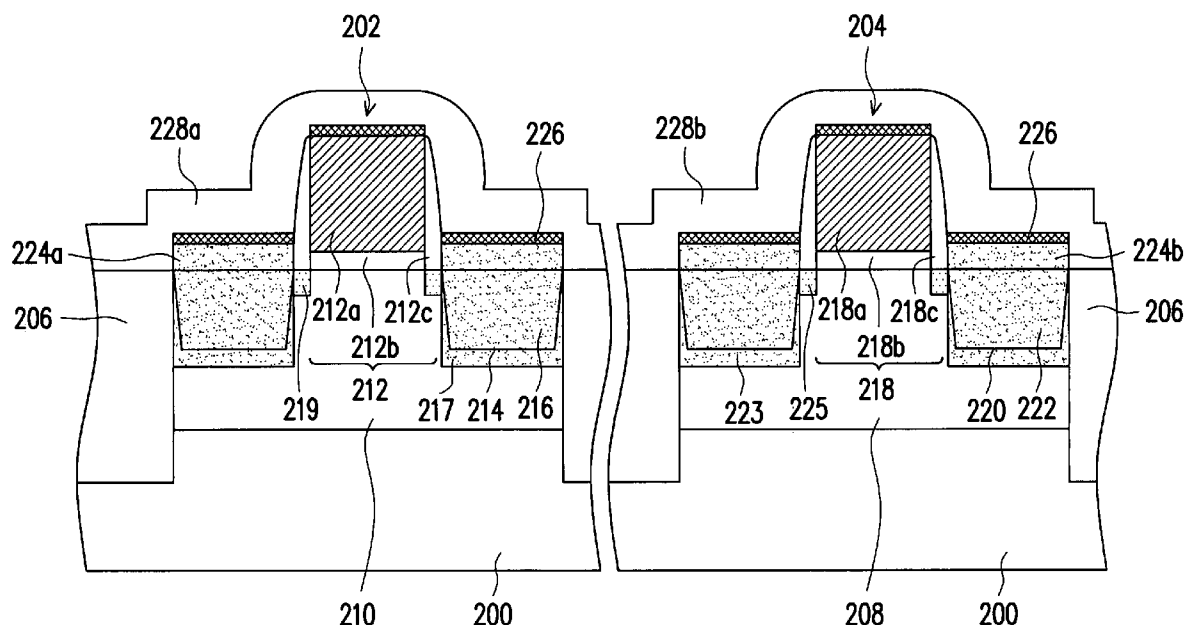
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(57) **ABSTRACT**

A semiconductor structure is disclosed, including a substrate having therein a first well of a first conductivity type and a second well of a second conductivity type, a first MOS transistor of the first conductivity type and a second MOS transistor of the second conductivity type. The first MOS transistor is disposed on the second well, including a gate structure on the second well and a strained layer of the first conductivity type in an opening in the second well beside the gate structure. The difference between the lattice parameter of a portion of the strained layer near the bottom of the opening and that of the substrate is less than the difference between the lattice parameter of a portion of the strained layer apart from the bottom of the opening and that of the substrate. The second MOS transistor is disposed on the first well.

14 Claims, 8 Drawing Sheets



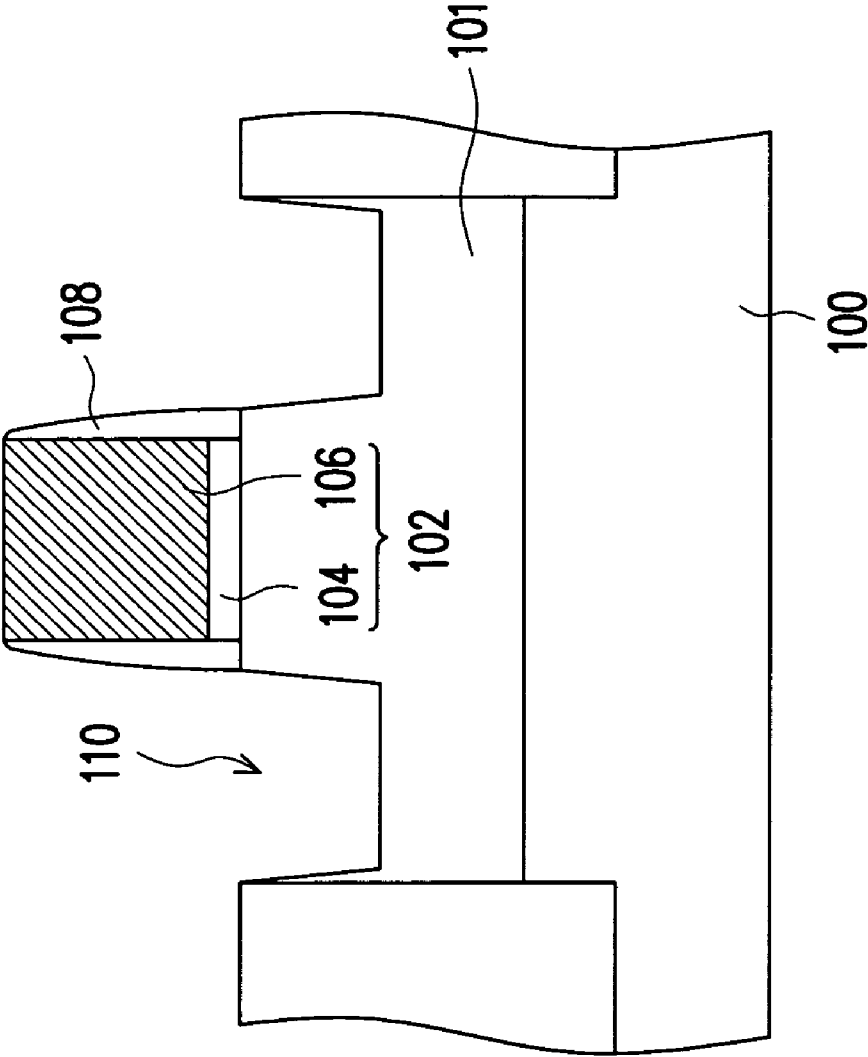


FIG. 1A (PRIOR ART)

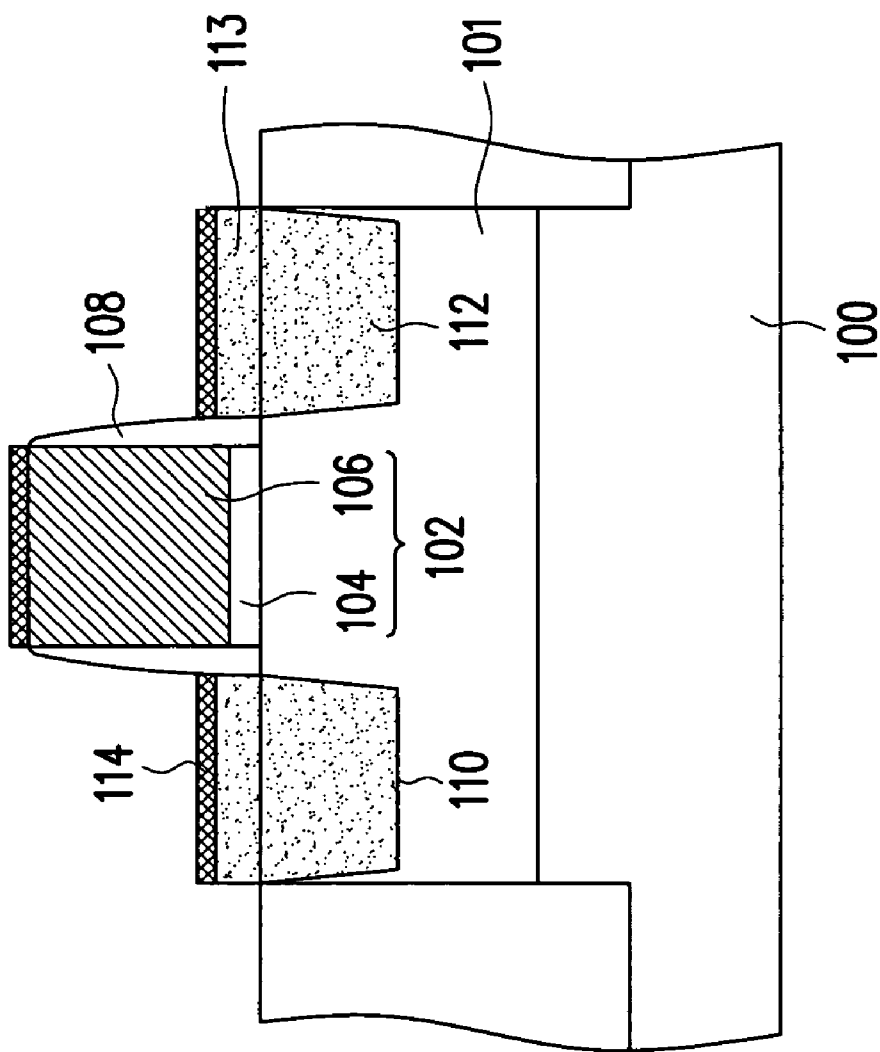


FIG. 1B (PRIOR ART)

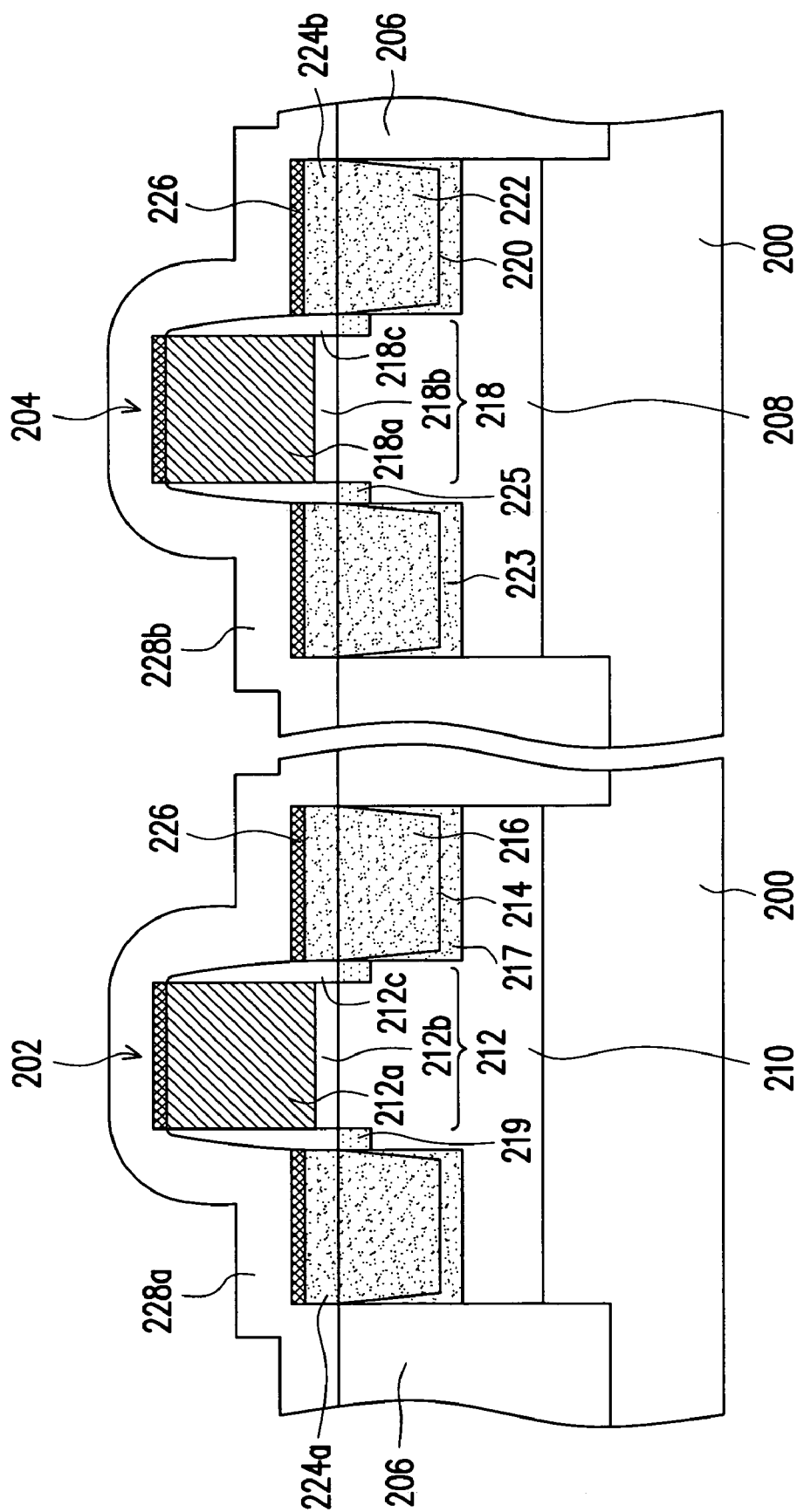


FIG. 2

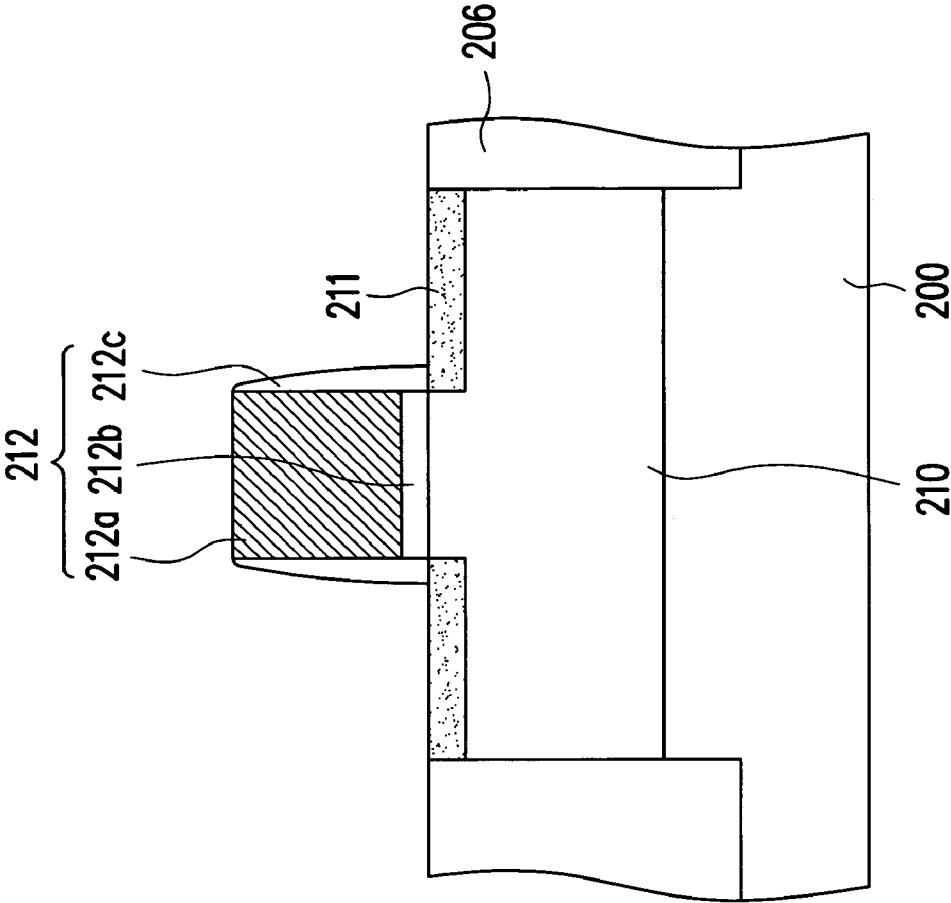


FIG. 3A

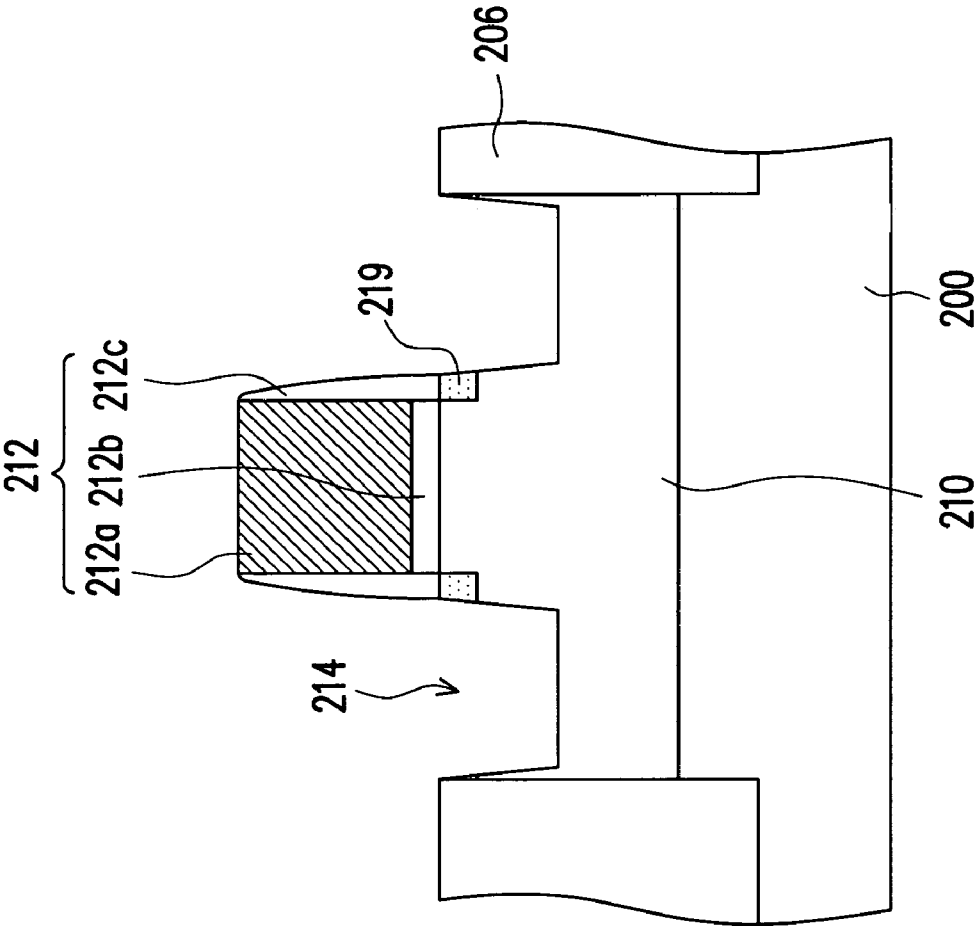


FIG. 3B

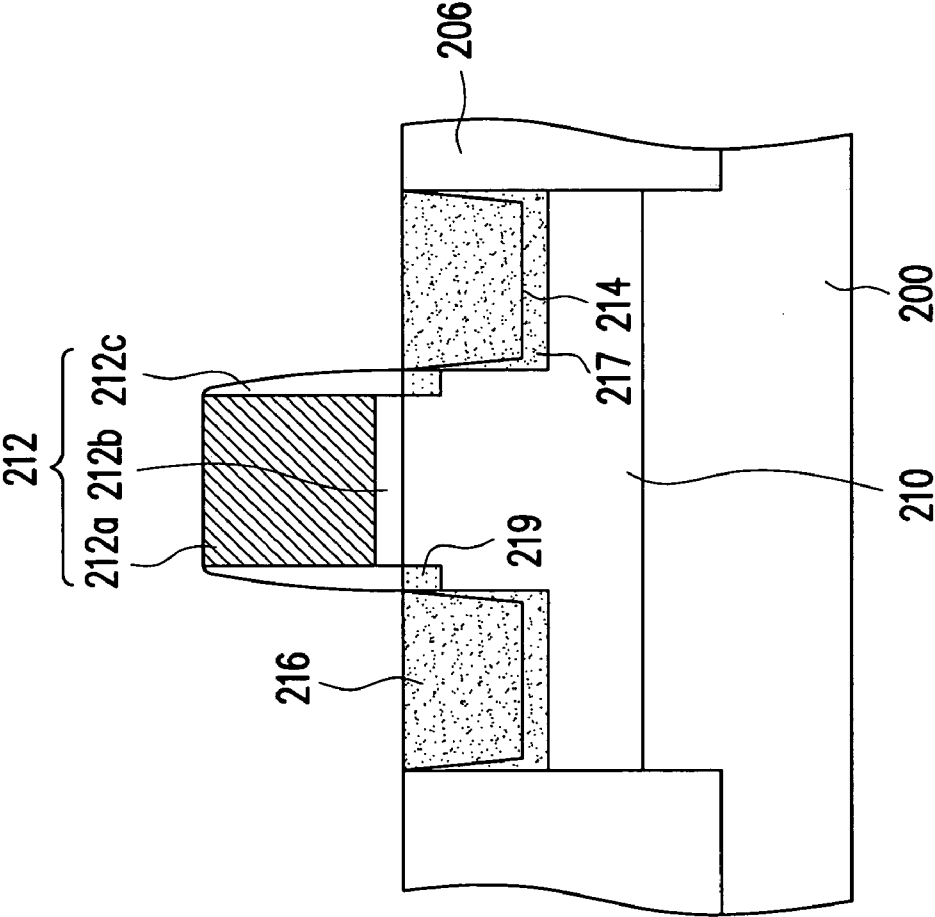


FIG. 3C

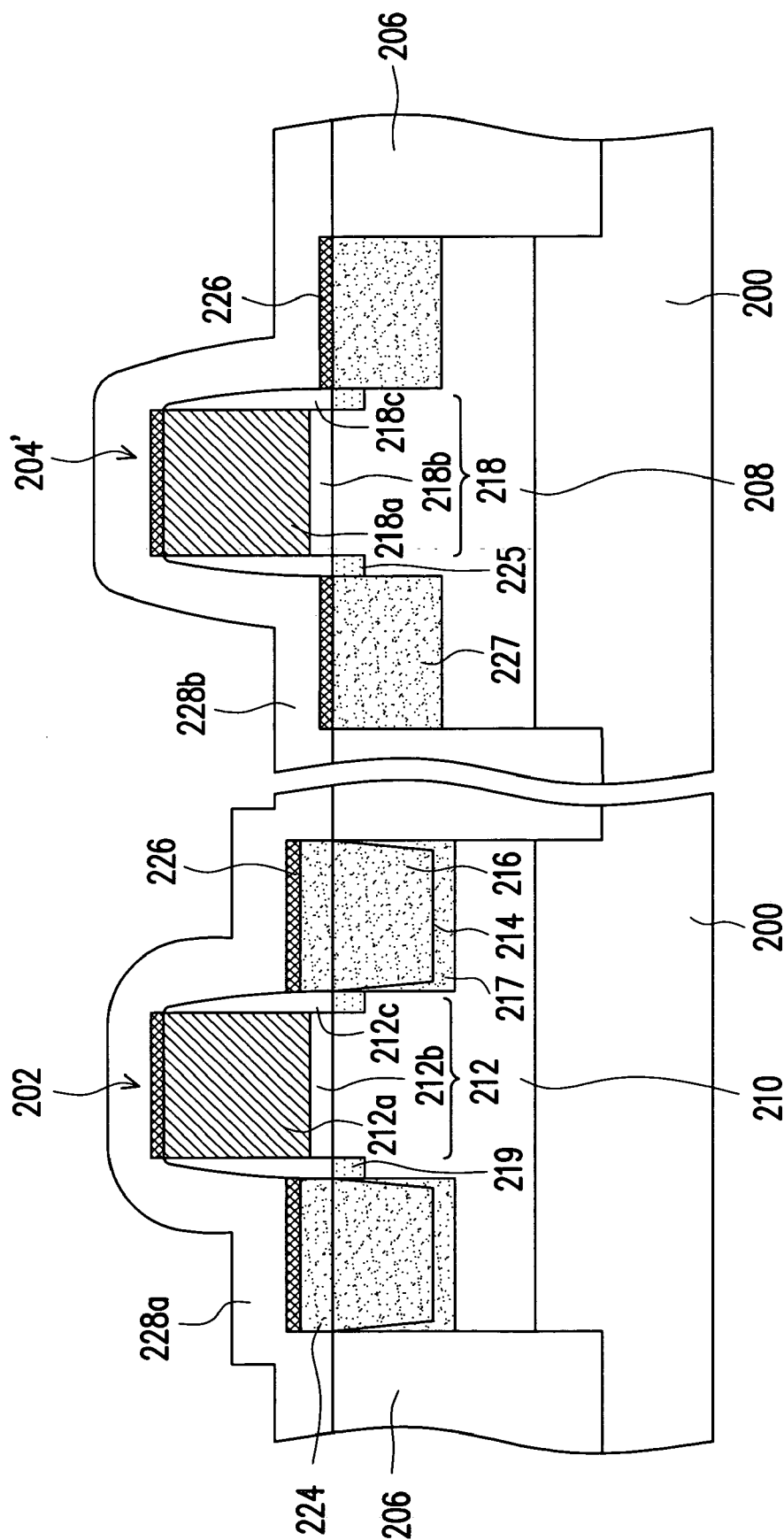


FIG. 4

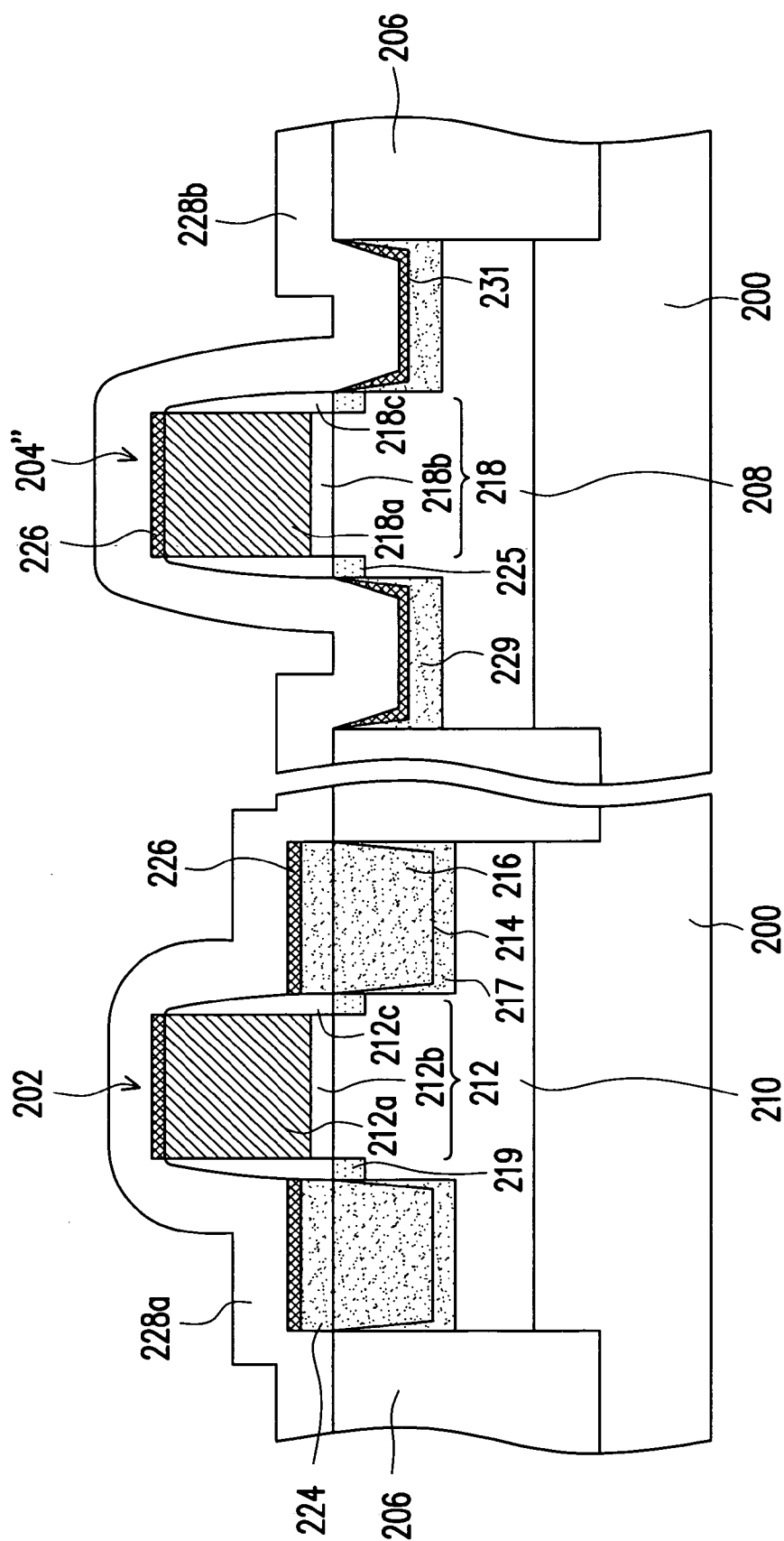


FIG. 5

1

SEMICONDUCTOR STRUCTURE AND FABRICATING METHOD THEREOF

BACKGROUND OF THE INVENTION

1. Field of the Invention

The present invention relates to a semiconductor structure and fabrication of the same. More particularly, the present invention relates to a semiconductor structure having a doped strained layer as a source/drain and a method for fabricating the same.

2. Description of the Related Art

Metal-oxide-semiconductor (MOS) transistors are essential to VLSI and ULSI circuits, and are widely used in microprocessors, semiconductor memory devices and power devices, etc., as basic constituent units. In some nanometer processes, the speed of a MOS transistor is increased by forming an opening in the substrate beside the gate structure and then filling the opening with a doped strained material as a source/drain (S/D) region to increase the carrier mobility of the S/D region.

FIGS. 1A-1B illustrate a process flow of fabricating a prior-art MOS transistor in a cross-sectional view. Referring to FIG. 1A, a substrate **100** with a well **101** therein is provided, and then a gate structure **102** including gate dielectric **104** and a gate **106** is formed on the well **101**. A spacer **108** is formed on the sidewall of the gate structure **102**, and then etching is conducted with the gate structure **102** and the spacer **108** as a mask to remove a portion of the exposed substrate **100** and form an opening **110**.

Referring to FIG. 1B, a doped strained layer **112** is formed in the opening **110** to serve as an S/D region, wherein a portion **113** of the doped strained layer **112** is above the surface of the substrate **100**. A (self-aligned silicide) salicide layer **114** is then formed on the gate structure **102** and the doped strained layer **112**.

Because the top surface of the doped strained layer **112** is higher than that of the substrate **100**, the stress caused by the salicide layer **114** is decreased. When the MOS transistor is PMOS, for example, to increase the compressive stress in the strained layer **112**, a SiGe layer with a Ge-content higher than 20% is formed as the strained layer **112**, or the thickness of the same is increased by increasing the depth of the opening **100**.

However, the thickness of a strained SiGe layer decreases with increase in the Ge-content thereof. Moreover, when the Ge-content is higher, the lattice parameter of the SiGe layer is larger making the difference between the lattice parameter of the SiGe layer and that of the substrate larger, so that defects easily occur at the interface of the SiGe layer and the substrate lowering the device performance. Furthermore, in a subsequent salicide process, the Ge-atoms will enter the metal silicide layer degrading its quality.

SUMMARY OF THE INVENTION

Accordingly, this invention provides a semiconductor structure that includes a doped strained layer with a non-uniform lattice parameter distribution as an S/D region for decreasing the difference between the lattice parameters of the S/D region and the substrate and thereby prevents defects from occurring at the interface of the two.

The semiconductor structure includes a substrate having therein a first well of a first conductivity type and a second well of a second conductivity type, a first MOS transistor of the first conductivity type and a second MOS transistor of the second conductivity type. The first MOS transistor is

2

disposed on the second well, including a first gate structure on the second well and a first strained layer of the first conductivity type in a first opening in the second well beside the first gate structure. The difference between the lattice parameter of a portion of the first strained layer near the bottom of the first opening and the lattice parameter of the substrate is smaller than the difference between the lattice parameter of a portion of the first strained layer apart from the bottom of the first opening and the lattice parameter of the substrate. The second MOS transistor is on the first well.

In a preferred embodiment, the lattice parameter of the first strained layer has a gradient distribution.

In embodiments where the first conductivity type is P-type, the lattice parameter of a portion of the first strained layer near the bottom of the first opening is smaller than that of a portion of the first strained layer apart from the bottom of the first opening. The material of such a first strained layer may be SiGe. In embodiments where the first conductivity type is N-type, the lattice parameter of a portion of the first strained layer near the bottom of the first opening is larger than that of a portion of the first strained layer apart from the bottom of the first opening. The material of such a first strained layer may be SiC.

In some embodiments, the above second MOS transistor includes a second gate structure on the first well and an S/D region of the second conductivity type in the first well beside the second gate structure. The above semiconductor structure may further include a silicon layer on the first strained layer and a metal silicide layer on the silicon layer, the S/D region and the first and the second gate structures.

In some embodiments, the above second MOS transistor includes a second gate structure on the first well and an S/D region of the second conductivity type around and under a second opening in the first well beside the second gate structure. The above semiconductor structure may also include a silicon layer on the first strained layer and a metal silicide layer on the silicon layer, the S/D region and the two gate structures.

In some embodiments, the above second MOS transistor includes a second gate structure on the first well and a second strained layer of the second conductivity type in a second opening in the first well beside the second gate structure. The difference between the lattice parameter of a portion of the second strained layer near the bottom of the second opening and the lattice parameter of the substrate is smaller than the difference between the lattice parameter of a portion of the second strained layer apart from the bottom of the second opening and the lattice parameter of the substrate. When the first conductivity type is P-type and the second one N-type, the lattice parameter of a portion of the first strained layer near the bottom of the first opening is smaller than that of a portion of the first strained layer apart from the bottom of the first opening, but the lattice parameter of a portion of the second strained layer near the bottom of the second opening is larger than that of a portion of the second strained layer apart from the bottom of the second opening. When the first conductivity type is N-type and the second one P-type, the lattice parameter of a portion of the first strained layer near the bottom of the first opening is larger than that of a portion of the first strained layer apart from the bottom of the first opening, but the lattice parameter of a portion of the second strained layer near the bottom of the second opening is smaller than that of a portion of the second strained layer apart from the bottom of the second opening. The lattice parameter of the second strained layer may also have a gradient distribution. In addition, the semiconductor structure may further include a silicon layer

3

on the first strained layer and the second strained layer, and a metal silicide layer on the silicon layer and the first and the second gate structures.

The method for fabricating a semiconductor structure of this invention is described as follows. A substrate having therein a first well of a first conductivity type and a second well of a second conductivity type is provided, and then a first gate structure is formed on the second well. A portion of the substrate beside the first gate structure is removed to form a first opening, and then a first epitaxy process is performed with a first mixed gas to form in the first opening a first strained layer containing silicon and a first IV-group element. The first mixed gas includes a first gas containing silicon and a second gas containing the first IV-group element, and the percentage of the second gas in the first mixed gas is increased with time during the first epitaxy process. In addition, a MOS transistor of the second conductivity type is formed on the first well.

In embodiments where the first conductivity type is P-type, the atomic size of the first IV-group element is larger than that of silicon increasing the lattice parameter, so that the first strained layer of P-type is subject to a compressive stress raising the hole mobility. In embodiments where the first conductivity type is N-type, the first IV-group element is carbon that has an atomic size smaller than that of silicon decreasing the lattice parameter, so that the first strained layer of N-type is subject to a tensile stress raising the electron mobility.

In a preferred embodiment, the first mixed gas further includes a first doping gas so that the first strained layer is formed having the first conductivity type. The MOS transistor of the second conductivity type may be formed by forming a second gate structure on the first well and then forming an S/D region of the second conductivity type in the first well beside the second gate structure. In addition, a silicon layer may be further formed on the first strained layer, and then a metal silicide layer may be formed on the silicon layer, the S/D region and the first and the second gate structures.

In some embodiments, the MOS transistor of the second conductivity type may be formed with the following steps. A second gate structure is formed on the first well, a portion of the substrate beside the second gate structure is removed to form a second opening, and then an S/D region of the second conductivity type is formed in the first well around and under the second opening. Similarly, a silicon layer may be further formed on the first strained layer, and then a metal silicide layer may be formed on the silicon layer, the S/D region and the first and the second gate structures.

In still some embodiments, the MOS transistor is formed with the following steps. A second gate structure is formed on the first well, a portion of the substrate beside the second gate structure is removed to form a second opening, and then a second epitaxy process is performed with a second mixed gas to form in the second opening a second strained layer containing silicon and a second IV-group element. The second mixed gas includes the first gas containing silicon and a third gas containing the second IV-group element, and the percentage of the third gas in the second mixed gas is increased with time during the second epitaxy process. When the first conductivity type is P-type and the second one N-type, the atomic size of the first IV-group element is larger than that of silicon but the second IV-group element is carbon that has an atomic size smaller than that of silicon. When the first conductivity type is N-type and the second one P-type, the first IV-group element is carbon that has an

4

atomic size smaller than that of silicon but the atomic size of the second IV-group element is larger than that of silicon.

In a preferred embodiment, the second mixed gas further includes a second doping gas so that the second strained layer is formed having the second conductivity type. In addition, a silicon layer may be further formed on the first strained layer and the second strained layer, and then a metal silicide layer may be formed on the silicon layer and the first and the second gate structures.

Accordingly, in the epitaxy process for forming a strained layer as an S/D region in this invention, the percentage of the gas containing the non-silicon IV-group element in the mixed gas is increased with time. Thereby, the difference between the lattice parameter of a portion of the strained layer near the bottom of the opening and the lattice parameter of the substrate is smaller than the difference between the lattice parameter of a portion of the strained layer apart from the bottom of the opening and the lattice parameter of the substrate. Thus, less defects occur at the interface of the strained layer and the substrate. Moreover, since a silicon layer is formed on the strained layer before the metal silicide layer is formed, the non-silicon IV-group element does not enter the metal silicide layer in the silicide process, so that the quality of the metal silicide layer is not degraded.

It is to be understood that both the foregoing general description and the following detailed description are exemplary, and are intended to provide further explanation of the invention as claimed.

BRIEF DESCRIPTION OF THE DRAWINGS

FIGS. 1A-1B illustrate a process flow of fabricating a prior-art MOS transistor in a cross-sectional view.

FIG. 2 illustrates a cross-sectional view of a semiconductor structure according to an embodiment of this invention.

FIGS. 3A-3C illustrate, in a cross-sectional view, a process flow of fabricating the MOS transistor **202** in FIG. 2 according to an embodiment of this invention.

FIG. 4 illustrates a cross-sectional view of a semiconductor structure according to another embodiment of this invention.

FIG. 5 illustrates a cross-sectional view of a semiconductor structure according to still another embodiment of this invention.

DESCRIPTION OF THE PREFERRED EMBODIMENTS

Referring to FIG. 2, the semiconductor structure of this embodiment includes a substrate **200**, a MOS transistor **202** of a first conductivity type, a MOS transistor **204** of a second conductivity type and an isolation structure **206**. The substrate **200** has a well **208** of the first conductivity type and a well **210** of the second conductivity type therein. The MOS transistor **202** is disposed on the well **210**, including a gate structure **212** on the well **210** and a doped strained layer **216** of the first conductivity type. The gate structure **212** includes a gate **212a** on the substrate **200**, gate dielectric **212b** between the gate **212a** and the substrate **200** and a spacer **212c** on the sidewall of the gate **212a**, and an opening **214** is formed in the well **210** beside the gate structure **212**. The gate **212a** may include poly-Si or metal, the gate dielectric **212b** may include SiO₂, SiN or SiON, and the spacer **212c** may include SiN.

The strained layer **216** is disposed in the opening **214** serving as a part of the S/D region of the MOS transistor **202**, wherein the difference between the lattice parameter of

5

a portion of the strained layer **216** near the bottom of the opening **214** and the lattice parameter of the substrate **200** is smaller than the difference between the lattice parameter of a portion of the strained layer **216** apart from the bottom of the opening **214** and the lattice parameter of the substrate **200**. It is more preferred that the lattice parameter of the strained layer **216** has a gradient distribution. When the first conductivity type is P-type, the strained layer **216** is a compressively strained layer, wherein a portion of the strained layer **216** near the bottom of the opening **214** has a lattice parameter equal to or larger than that of the substrate **200** but smaller than that of a portion of the strained layer **216** apart from the bottom of the opening **214**. When the first conductivity type is N-type, the strained layer **216** is a tensily strained layer, wherein a portion of the strained layer **216** near the bottom of the opening **214** has a lattice parameter equal to or smaller than that of the substrate **200** but larger than that of a portion of the strained layer **216** apart from the bottom of the opening **214**. The MOS transistor **202** also includes a doped region **217** of the first conductivity type under and around the opening **214** as another part of its S/D region, and an S/D extension region **219** of the first conductivity type in the well **210** under the spacer **212c**.

The MOS transistor **204** is disposed on the well **208**. The isolation structure **206** is disposed in the substrate **200** to define the active areas of the devices, and may be an STI structure or other type of isolation structure. The MOS transistor **204** includes a gate structure **218** and a doped strained layer **222** of the second conductivity type. The gate structure **218** is disposed on the well **208**, and an opening **220** is formed in the well **208** beside the gate structure **218**. The gate structure **218** includes gate dielectric **218b**, a gate **218a** on the gate dielectric **218b** and a spacer **218c** on the sidewall of the gate **218a**, wherein possible materials of **218a**, **218b** and **218c** are the same as above.

The strained layer **222** is disposed in the opening **220** serving as a part of the S/D of the MOS transistor **204**. Similarly, the difference between the lattice parameter of a portion of the strained layer **222** near the bottom of the opening **220** and the lattice parameter of the substrate **200** is smaller than the difference between the lattice parameter of a portion of the strained layer **222** apart from the bottom of the opening **220** and the lattice parameter of the substrate **200**. However, the lattice parameter of the strained layer **222** changes reversely with respect to that of the strained layer **216**. Specifically, when the first conductivity type is P-type and the second one N-type, the strained layer **216** is a compressively strained layer with the lattice parameter increasing toward its top, while the strained layer **222** is a tensily strained layer with the lattice parameter decreasing toward its top. When the first conductivity type is N-type and the second one P-type, the strained layer **216** is a tensily strained layer just mentioned, while the strained layer **222** is a compressively strained layer just mentioned. The MOS transistor **204** also includes a doped region **223** of the second conductivity type under and around the opening **220** as another part of the S/D region of the MOS transistor **204**, and an S/D extension region **225** of the second conductivity type in the well **208** under the spacer **218c**.

It is noted that in this embodiment, when the first conductivity type is P-type and the second one N-type, the compressively strained layer **216** may include SiGe that is larger in lattice parameter relative to pure silicon, while the tensily strained layer **222** may include SiC that is smaller in lattice parameter relative to pure silicon. When the first conductivity type is N-type and the second one P-type, the

6

tensily strained layer **216** may include SiC, while the compressively strained layer **222** may include SiGe.

Moreover, on the strained layers **216** and **222** two silicon layers **224a** and **224b** with corresponding conductivity types may be disposed respectively, and a metal silicide layer **226** may further be disposed on the silicon layers **224a** and **224b** and the gate structures **212** and **218**. The thickness of the silicon layer **224a** or **224b** may range from 100 Å to 500 Å. The material of the metal silicide layer **226** may be WSi, TiSi, MoSi, NiSi, PdSi or PtSi. Moreover, contact etching stop layers **228a** and **228b** may further be disposed over the substrate **200** covering the resulting structure. The material of the contact etching stop layer **228a** or **228b** may be SiN, and the contact etching stop layer **228a/228b** may be a compressive or tensile layer for increasing the carrier mobility in the channel layer of the MOS transistor **202/204** and thereby further improves the performance of the MOS transistor **202/204**.

An example of fabricating the semiconductor structure in FIG. **2** is described as follows. Since the left half and the right half of the semiconductor structure is similar in structure, the fabricating process of the left half is described firstly.

FIGS. **3A-3C** illustrate, in a cross-sectional view, a process flow of fabricating the MOS transistor **202** in FIG. **2**. Referring to FIG. **3A**, a substrate **200** is provided, having therein a well of the first conductivity type (not shown), a well **210** of the second conductivity type and an isolation structure **206** defining the active areas of the devices. The wells can be formed through ion implantation, and the isolation structure **206** may be formed through an STI process. A gate **212a** and gate dielectric **212b** are formed on the well **210**, possibly by forming a layer of gate dielectric material and a gate material layer on the substrate **200** and then sequentially patterning the two layers.

Referring to FIG. **3A** again, a doped region **211** of the first conductivity type is formed in the well **210** beside the gate **212a**, possibly through an ion implantation with the gate **212a** as a mask. A spacer **212c** is formed on the sidewall of the gate **212a**, constituting a gate structure **212** together with the gate **212a** and gate dielectric **212b**.

Referring to FIG. **3B**, a portion of the substrate **200** beside the gate structure **212** is removed to form an opening **214**, while a portion of the doped region **211** is removed to form an S/D extension region **219**. The opening **214** may be formed with the following steps. A patterned photoresist layer (not shown) is formed over the substrate **200**, exposing the gate structure **212** and the region for forming the opening **214**. An etching process is conducted with the gate structure **212** and the patterned photoresist layer as a mask to remove a portion of the substrate **200**, wherein the etching may be isotropic, anisotropic or tilted etching. The depth of the opening **214** is usually 100-1000 Å, preferably 300-500 Å.

Referring to FIG. **3C**, ion implantation is conducted with the gate structure **212** as a mask to implant a dopant of the first conductivity type into a portion of the substrate **200** under and around the opening **214** to form a doped region **217** as a part of the S/D region of the MOS transistor **202**. It is particularly noted that the above ion implantation can alternatively be conducted before the opening **214** is formed, wherein the depth of the opening **214** has to be controlled smaller than that of the implantation.

Thereafter, a first epitaxy process is conducted with a first mixed gas to form a strained layer **216** in the opening **214**, wherein the first mixed gas includes a first gas containing silicon and a second gas containing a first IV-group element and the percentage of the second gas in the first mixed gas

is increased with time during the first epitaxy process. The first gas is, for example, silane or disilane. The first mixed gas preferably further includes a first doping gas so that the strained layer **216** is formed having the first conductivity type. When the first conductivity type is P-type, the first IV-group element is one having an atomic size larger than that of silicon, such as Ge, so that the lattice parameter is increased and a compressively strained layer **216** is formed with improved hole mobility. When the first conductivity type is N-type, the IV-group element is carbon that is smaller than silicon in atomic size, so that the lattice parameter is decreased and a tensily strained layer **216** is formed with improved electron mobility.

The fabricating process of the MOS transistor **204** is analogous to that of the MOS transistor **202**. The main differences are that the MOS transistor **204** has an opposite conductivity type and the strained layer **222** thereof is formed with a second epitaxy process that uses a second mixed gas that includes the first gas containing Si and a third gas containing a second IV-group element. Similarly, the second mixed gas may further include a second doping gas, so that the strained layer **222** is formed having the second conductivity type. To respectively form a compressively strained layer required by PMOS and a tensily strained layer required by NMOS, when the first conductivity type is P-type and the second one N-type, the atomic size of the first IV-group element is larger than that of silicon to result in a larger lattice parameter, while the second IV-group element is carbon that has an atomic size smaller than that of silicon to result in a smaller lattice parameter. On the contrary, when the first conductivity type is N-type and the second one P-type, the first IV-group element is carbon, and the atomic size of the second IV-group element is larger than that of silicon.

Moreover, when the first conductivity type is P-type and the second one N-type, the second gas may be GeH_4 , and the second gas in the first mixed gas may be increased from 0 to 40% with time during the first epitaxy process, while the first doping gas may be B_2H_6 . The third gas may be CH_4 or C_2H_6 , and the third gas in the second mixed gas may be increased from 0 to 20% with time during the second epitaxy process, while the second doping gas may be PH_3 .

On the contrary, when the first conductivity type is N-type and the second one P-type, the second gas may be CH_4 or C_2H_6 , and the second gas in the first mixed gas may be increased from 0 to 20% with time during the first epitaxy process, while the first doping gas may be PH_3 . The third gas may be GeH_4 , and the third gas in the second mixed gas may be increased from 0 to 40% with time during the second epitaxy process, while the second doping gas may be B_2H_6 .

It is also noted that the MOS transistors **202** and **204** are not restricted to form in two separate processes. The fabricating process of the MOS transistor **202** is usually integrated more or less with that of the MOS transistor **204** for step simplification.

After the MOS transistor **202** (or **204**) is formed, a silicon layer **224a** (or **224b**) of the same conductivity type may be further formed on the strained layer **216** (or **222**), as shown in FIG. 2. The silicon layer **224a** (or **224b**) may be formed directly in the first (or second) epitaxy process by stopping supplying the second (or third) gas after the strained layer **216** (or **222**) is formed but continuing to supply the Si-containing first gas and the first (or second) doping gas for epitaxy. After the silicon layers **224a** and **224b** are formed, a metal silicide layer **226** can be further formed, possibly through a silicide process, on the silicon layers **224a** and **224b** and the gate structures **212** and **218**, as shown in FIG. 2. After the metal silicide layer **226** is formed, contact etching stop layers **228a** and **228b** may be formed over the

substrate **200** covering the resulting structure, as shown in FIG. 2, possibly through chemical vapor deposition (CVD).

It is also noted that the MOS transistor **202** of the first conductivity type having a strained S/D region of non-uniform lattice parameter is not restricted to form together with a MOS transistor of the second conductivity type also having a strained S/D region of non-uniform lattice parameter. The MOS transistor **202** may alternatively be formed together with a structurally different MOS transistor of the second conductivity type. Such examples are described in the following embodiments.

FIG. 4 illustrates a cross-sectional view of a semiconductor structure according to another embodiment of this invention. The MOS transistor **204'** in replacement of the MOS transistor **204** includes a gate structure **218** as mentioned above and an S/D region **227** in the well **208** beside the gate structure **218**. The MOS transistor **204'** also includes an S/D extension region **225** of the second conductivity type in the well **208** under the spacer **218c**. Similarly, in this embodiment, the strained layer **216** may also be formed with a silicon layer **224** thereon, and then a metal silicide layer **226** may be further formed on the silicon layer **224**, the S/D region **227** and the gate structures **212** and **218**. The thickness of the silicon layer **224** and the material of the metal silicide layer **226** may be the same as above. Moreover, two contact etching stop layers **228a** and **228b**, such as SiN layers formed with different recipes to have different stresses, can be formed over the substrate **200** covering the MOS transistors **202** and **204'**.

The MOS transistor **204'** may be formed by forming a gate structure **218** on the well **208** and then forming, possibly through an ion implantation process using the gate structure **218** as a mask, an S/D region **227** of the second conductivity type in the well **208** beside the gate structure **218**.

FIG. 5 illustrates a cross-sectional view of a semiconductor structure according to yet another embodiment of this invention. The MOS transistor **204''** in replacement of the MOS transistor **204** includes a gate structure **218** as mentioned above and an S/D region **229** in the well **208** under and around an opening **231** beside the gate structure **218**. The transistor **204''** also includes an S/D extension region **225** of the second conductivity type in the well **208** under the spacer **218c**. In the present embodiment, the strained layer **216** may similarly be formed with a silicon layer **224** thereon, and then a metal silicide layer **226** may be further formed on the silicon layer **224**, the S/D region **229** and the gate structures **212** and **218**. The thickness of the silicon layer **224** and the material of the metal silicide layer **226** may be the same as above. Moreover, contact etching stop layers **228a** and **228b** as mentioned above may be further formed over the substrate **200** covering the MOS transistors **202** and **204''**, respectively. The contact etching stop layer **228b** preferably has a thickness at least sufficient to fill up the opening **231** to apply a sufficient large stress to the channel layer of the MOS transistor **204''** and effectively increase the carrier mobility in the channel layer thereby.

In addition, the MOS transistor **204''** may be formed with the following steps. A gate structure **218** is formed on the well **208**, a portion of the substrate **200** beside the gate structure **218** is removed to form an opening **231**, and then an S/D region **229** of the second conductivity type is formed in the well **208** under and around the opening **231**, possibly with an ion implantation process using the gate structure **218** as a mask.

It is also noted that the MOS transistors **202** and **204'** (or **204''**) are either not restricted to form in two separate processes. The fabricating process of the MOS transistor **202** is usually integrated more or less with that of the MOS transistor **204'** (or **204''**) for step simplification.

Nevertheless, it is particularly noted that the MOS transistor **202** with a strained S/D region of non-uniform lattice parameter can alternatively be formed together with a MOS transistor of opposite conductivity type that has a structure similar to that of the MOS transistor **204** in FIG. **2** but has a strained S/D region of uniform lattice parameter.

Accordingly, in the epitaxy process for forming a strained layer as an S/D region in this invention, the percentage of the gas containing the non-silicon IV-group element in the mixed gas for epitaxy is increased with time. Thereby, the difference between the lattice parameter of a portion of the strained layer near the bottom of the opening and the lattice parameter of the substrate is smaller than the difference between the lattice parameter of a portion of the strained layer apart from the bottom of the opening and the lattice parameter of the substrate. Thus, less defects occur at the interface of the strained layer and the substrate.

Moreover, since a silicon layer is formed on the strained layer before the metal silicide layer is formed, the non-silicon IV-group element does not enter the metal silicide layer in the silicide process, so that the quality of the metal silicide layer is not degraded.

It will be apparent to those skilled in the art that various modifications and variations can be made to the structure of the present invention without departing from the scope or spirit of the invention. In view of the foregoing, it is intended that the present invention covers modifications and variations of this invention provided they fall within the scope of the following claims and their equivalents.

What is claimed is:

1. A semiconductor structure, comprising:
 - a substrate, having therein a first well of a first conductivity type and a second well of a second conductivity type;
 - a first MOS transistor of the first conductivity type on the second well, comprising:
 - a first gate structure on the second well; and
 - a first strained layer of the first conductivity type in a first opening in the second well beside the first gate structure, wherein a difference between a lattice parameter of a portion of the first strained layer near a bottom of the first opening and a lattice parameter of the substrate is smaller than a difference between a lattice parameter of a portion of the first strained layer apart from the bottom of the first opening and the lattice parameter of the substrate; and
 - a second MOS transistor of the second conductivity type on the first well.
2. The semiconductor structure of claim **1**, wherein the lattice parameter of the first strained layer has a gradient distribution.
3. The semiconductor structure of claim **1**, wherein the first conductivity type is P-type, and the lattice parameter of a portion of the first strained layer near the bottom of the first opening is smaller than the lattice parameter of a portion of the first strained layer apart from the bottom of the first opening.
4. The semiconductor structure of claim **3**, wherein the first strained layer comprises SiGe.
5. The semiconductor structure of claim **1**, wherein the first conductivity type is N-type, and the lattice parameter of a portion of the first strained layer near the bottom of the first opening is larger than the lattice parameter of a portion of the first strained layer apart from the bottom of the first opening.
6. The semiconductor structure of claim **5**, wherein the first strained layer comprises SiC.

7. The semiconductor structure of claim **1**, wherein the second MOS transistor comprises:

- a second gate structure on the first well; and
- a source/drain region of the second conductivity type in the first well beside the second gate structure.

8. The semiconductor structure of claim **7**, further comprising:

- a silicon layer on the first strained layer; and
- a metal silicide layer on the silicon layer, the source/drain region and the first and the second gate structures.

9. The semiconductor structure of claim **1**, wherein the second MOS transistor comprises:

- a second gate structure on the first well; and
- a source/drain region of the second conductivity type around and under a second opening in the first well beside the second gate structure.

10. The semiconductor structure of claim **9**, further comprising:

- a silicon layer on the first strained layer; and
- a metal silicide layer on the silicon layer, the source/drain region and the first and the second gate structures.

11. The semiconductor structure of claim **1**, wherein the second MOS transistor comprises:

- a second gate structure on the first well; and
- a second strained layer of the second conductivity type in a second opening in the first well beside the second gate structure.

12. The semiconductor structure of claim **11**, wherein a difference between a lattice parameter of a portion of the second strained layer near a bottom of the second opening and the lattice parameter of the substrate is smaller than a difference between a lattice parameter of a portion of the second strained layer apart from the bottom of the second opening and the lattice parameter of the substrate;

when the first conductivity type is P-type and the second conductivity type is N-type, the lattice parameter of a portion of the first strained layer near the bottom of the first opening is smaller than the lattice parameter of a portion of the first strained layer apart from the bottom of the first opening, but the lattice parameter of a portion of the second strained layer near the bottom of the second opening is larger than the lattice parameter of a portion of the second strained layer apart from the bottom of the second opening; and

when the first conductivity type is N-type and the second conductivity type is P-type, the lattice parameter of a portion of the first strained layer near the bottom of the first opening is larger than the lattice parameter of a portion of the first strained layer apart from the bottom of the first opening, but the lattice parameter of a portion of the second strained layer near the bottom of the second opening is smaller than the lattice parameter of a portion of the second strained layer apart from the bottom of the second opening.

13. The semiconductor structure of claim **12**, wherein the lattice parameter of the second strained layer has a gradient distribution.

14. The semiconductor structure of claim **11**, further comprising:

- a silicon layer on the first strained layer and the second strained layer; and
- a metal silicide layer on the silicon layer and the first and second gate structures.